

Title (en)  
GALVANIC BATH, METHOD FOR GALVANIC DEPOSITION, AND USE OF A BIPOLAR MEMBRANE FOR SEPARATING IN A GALVANIC BATH

Title (de)  
GALVANISCHES BAD, VERFAHREN ZUR GALVANISCHEN ABSCHIEDUNG UND VERWENDUNG EINER BIPOLAREN MEMBRAN ZUR SEPARATION IN EINEM GALVANISCHEN BAD

Title (fr)  
BAIN GALVANIQUE, PROCÉDÉ DE DÉPÔT GALVANIQUE ET UTILISATION D'UNE MEMBRANE BIPOLAIRE POUR LA SÉPARATION DANS UN BAIN GALVANIQUE

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Application  
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Abstract (en)  
[origin: WO2009077146A2] The invention relates to an alkali, galvanic bath for applying zinc or zinc alloys to substrates, wherein the anode chamber and the cathode chamber are separated from each other by a bipolar membrane. The galvanic bath is operated with zinc or zinc alloy baths that can comprise further additives. The invention further relates to a method for galvanic deposition of zinc or zinc alloys on substrates, wherein the substrate is placed in the galvanic bath according to the invention. The invention further relates to the use of bipolar membranes for separating the anode chamber and cathode chamber in galvanic baths, and for avoiding anodic disintegration of organic components of the electrolyte in galvanic baths.

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